#### **Current Transfer Ratio**

	Cu				
Classification	Ta = 25°C		Ta = -25 to 75°C	Marking of	
(Note 1)		I <sub>F</sub> = 0.5 mA V <sub>CE</sub> = 1.5 V	$I_F = 1 \text{ mA}$ $V_{CE} = 0.5 \text{ V}$	Classification	
Rank BV	200%	100%	100%	BV	
Standard	100%	50%	50%	BV, Blank	

Note 1: Ex, rank BV: TLP124(BV)

Note: Application type name for certification test, please use standard product type name, i, e.

TLP124(BV): TLP124

## Absolute Maximum Ratings (Ta = 25°C)

	Characteristics	Symbol	Rating	Unit
	Forward current	l <sub>F</sub>	50	mA
	Forward current derating (Ta ≥ 53°C)	ΔI <sub>F</sub> /°C	-0.7	mA/°C
ED	Peak forward current (100 µs pulse, 100 pps)	lfp	1	A
۳	Reverse voltage	V <sub>R</sub>	5	(A)
	Diode power dissipation	PD	100	mW
	Diode power dissipation derating (Ta $\geq$ 53°C)	ΔPp/°C	-1,39	mW/°C
	Junction temperature	Ŧį	125	°C
	Collector-emitter voltage	VCEO	80	V
	Emitter-collector voltage	VECO	7	V
	Collector current	lc	50	mA
Detector	Peak collector current (10 ms pulse, 100 pps)	ICP	100	mA
Ğ	Power dissipation	Pc	150	mW
	Power dissipation defating (Ta ≥ 25°C)	ΔPc/°C	-1.5	mW/°C
	Junction temperature		125	°C
Stor	rage temperature range	Tstg	-55 to 125	°C
Оре	erating temperature range	Topr	-55 to 100	°C
Lea	d soldering temperature (10 s)	T <sub>sol</sub>	260	°C
Tota	al package power dissipation	Рт	200	mW
	al package power dissipation (Ta ≥ 25°C)	ΔPτ/°C	-2.0	mW/°C
	ation voltage , 60 s, R,H. ≤ 60 %) (Note 1)	BVs	3750	Vrms

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc.).

Note 1: Device considered a two terminal device: Pins1, 3 shorted together and pins 4, 6 shorted together.



### **Recommended Operating Conditions**

Characteristics	Symbol	Min	Тур.	Max	Unit
Supply voltage	Vcc	_	5	48	V
Forward current	lF	_	1.6	20	mA
Collector current	Ic	_	1	10	mA
Operating temperature	Topr	-25	_	75	°C

Note: Recommended operating conditions are given as a design guideline to obtain expected performance of the device. Additionally, each item is an independent guideline respectively. In developing designs using this product, please confirm specified characteristics shown in this document.

## **Electrical Characteristics (Ta = 25°C)**

	Characteristics	Symbol	Test Condition	Min	Typ.	Max	Unit
	Forward voltage	VF	IF = 10 mA	1.0	1.15	1.3	V
LED	Reverse Current	IR	VR = 5 V	+(	))	10	μΑ
	Capacitance	CT	V = 0 V, f = 1 MHz	( <del>-</del>	30//	_	pF
	Collector-emitter breakdown voltage	V <sub>(BR)</sub> CEO	Ic = 0.5 mA	80	) (	_	V
ō	Emitter-collector breakdown voltage	V <sub>(BR)ECO</sub>	IE = 0.1 mA	$\langle \mathcal{J} \rangle$	_	_	V
Detector	Collector dark current	lana	V <sub>CE</sub> = 48 V	)	10	100	nA
Collector dark current	ICEO	V <sub>CE</sub> = 48 V, Ta = 85 °C	) —	2	50	μΑ	
	Capacitance collector to emitter	CCE	V = 0 V, f = 1 MHz	_	12	_	pF

## Coupled Electrical Characteristics (Ta = 25°C)

Characteristics	Symbol	Test Condition		Min	Тур.	Max	Unit
Compart transfer ratio	\ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \	IF = 1 mA, VCE = 0.5 V		100	_	1200	0/
Current transfer ratio	IC/IF		Rank BV	200	_	1200	%
Low input CTR	lo/le/	I <sub>F</sub> = 0.5 mA, V <sub>CE</sub> = 1.5 V		50		_	%
Low Input CTK	IC/IF(low)		Rank BV	100		_	70
		Ic = 0.5 mA, I <sub>F</sub> = 1 mA		_		0.4	
Collector-emitter saturation voltage	V <sub>CE(sat)</sub>	IÇ = 1 mA, IF = 1 mA		_	0.2		V
2/\\)	$\wedge$	V	Rank BV	_		0.4	
Off-state collector current	IC(off)	VF = 0.7 V, VCE = 48 V		_		10	μΑ

# Coupled Electrical Characteristics (Ta = -25 to 75°C)

Characteristic	Symbol	Test Condition	Min	Тур.	Max	Unit
Current transfer ratio	lo/le	I <sub>F</sub> = 1 mA, V <sub>CE</sub> = 0.5 V	50	_	_	%
Current transfer fatio	IC/IF	Rank BV	100	_	_	%
Low input CTR	lo/le#	I <sub>F</sub> = 0.5 mA, V <sub>CE</sub> = 1.5 V	_	50	_	%
Low input GTK	IC/I <sub>F(low)</sub>	Rank BV	_	100	_	%

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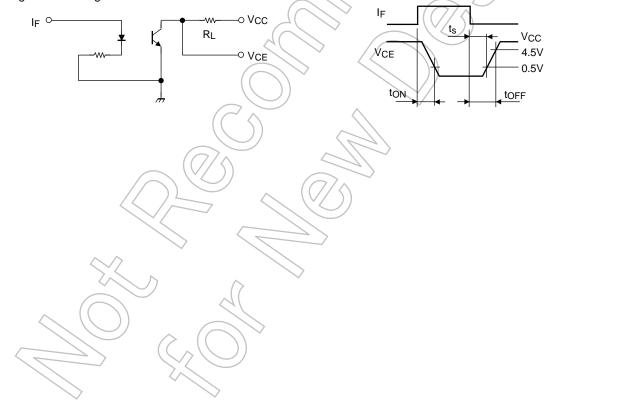
# Isolation Characteristics (Ta = 25°C)

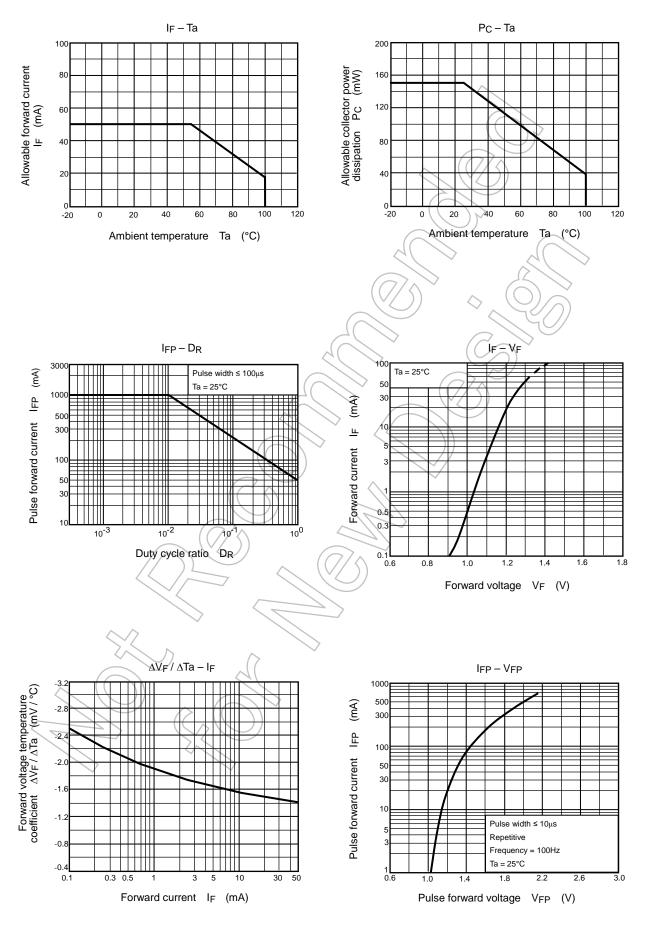
Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Capacitance (input to output)	Cs	Vs = 0 V, f = 1 MHz	_	0.8	_	pF
Isolation resistance	Rs	V <sub>S</sub> = 500 V, R.H. ≤ 60 %	5×10 <sup>10</sup>	10 <sup>14</sup>	_	Ω
Isolation voltage	BVs	AC, 60 s	3750	_	_	V <sub>rms</sub>

# **Switching Characteristics (Ta = 25°C)**

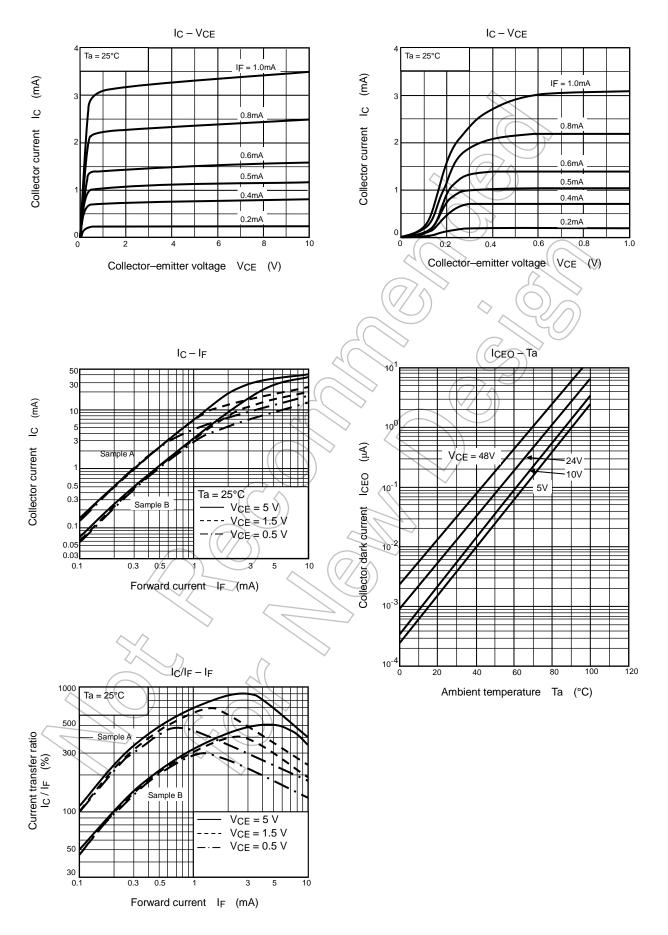
Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Rise time	t <sub>r</sub>	(())	_	8	_	
Fall time	tf	V <sub>CC</sub> = 10 V, I <sub>C</sub> = 2 mA	_	8	_	
Turn-on time	ton	R <sub>L</sub> = 100 Ω	_	(10	4	μs
Turn-off time	toff		-52	8	_	
Turn-on time	toN		+(	))10	_	
Storage time	ts	$R_L = 4.7 \text{ k}\Omega$ (Fig.1) $V_{CC} = 5 \text{ V}, I_F = 1.6 \text{ mA}$	( <del>-</del>	50//	_	μs
Turn-off time	tOFF	VCC - 5 V, IF - 1.0 IIIA	7	300	_	

Fig. 1 Switching time test circuit

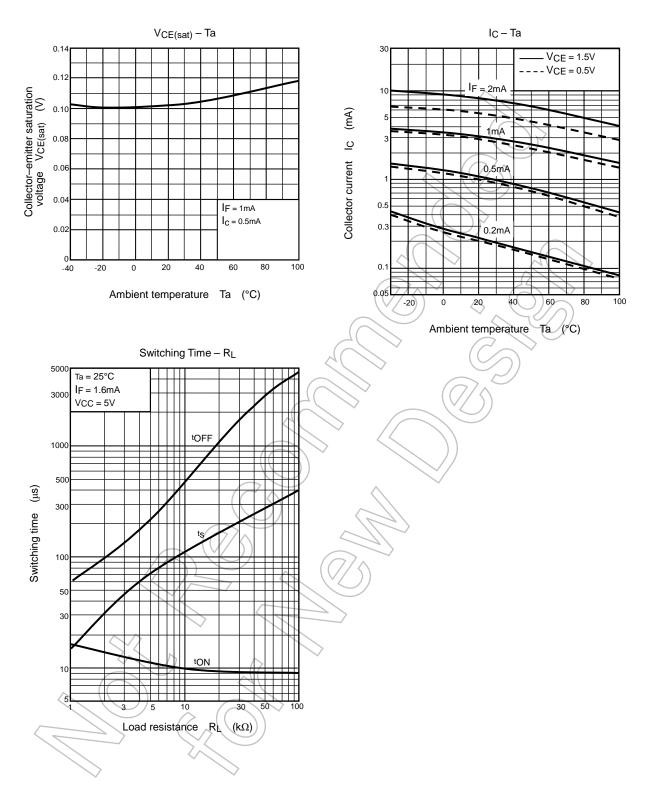




NOTE: The above characteristics curves are presented for reference only and not guaranteed by production test, unless otherwise noted.



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